1. (Twice Amended) A semiconductor device, comprising:

a main conductor layer having an end that is electrically connected to an electrode pad;

an insulating layer having an opening section on said main conductor layer; and

a protrudent electrode electrically connected to said main conductor layer via said opening section, said protrudent electrode being made of Sn or a metal having Sn as its main component,

B1

said semiconductor device further comprising:

a metal layer completely covering a bottom surface, but not side surfaces, of the opening section on the main conductor layer so that said metal layer is provided between said main conductor layer and said protrudent electrode.

B2

2. (Amended) The semiconductor device as set forth in Claim 1, wherein:

said metal layer is made of Au or a metal having Au as its main component.

17. (Amended) A semiconductor device, comprising:

a conductive wiring layer connected to an electrode pad formed on a semiconductor substrate;

B3

an insulating layer formed on the wiring layer and having an opening therein which exposes an upper surface portion of the wiring layer;

a metal layer completely covering the upper surface portion of the wiring layer exposed by the opening, but not side surfaces of the opening; and

a protruding electrode electrically connected to the wiring layer via the metal layer, the protruding electrode being made of Sn or a metal having Sn as its main component.